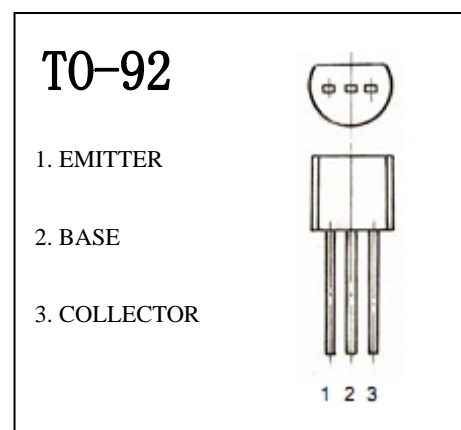


深圳市晶泰源电子有限公司

8550C TRANSISTOR(PNP)

MAXIMUM RATINGS(Ta=25°C unless otherwise noted)

Symbol	Parameter	Value	Units
VCBO	Collector-Base Voltage	-40	V
VCEO	Collector-Emitter Voltage	-25	V
VEBO	Emitter-Base Voltage	-5	V
IC	Collector Current	-0.5	A
PC	Collector Power Dissipation	625	mW
Tj	Junction Temperature	150	°C
Tstg	Storage Temperature	-55~150	°C



ELECTRICAL CHARACTERISTICS(Tamb=25°C unless otherwise specified):

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	V(BR)CBO	IC=-100uA, IE=0	-40			V
Collector-emitter breakdown voltage	V(BR)CEO	IC=-1mA, IB=0	-25			V
Emitter-base breakdown voltage	V(BR)EBO	IC=-100uA, IC=0	-5			V
Collector cut-off current	ICBO	VCB=-40V, IE=0			-0.1	μA
Emitter cut-off current	IEBO	VEB=-5V, IC=0			-0.1	μA
DC current gain	HFE	Vce=-1V, IC=-50mA	120		200	
Collector-emitter saturation voltage	VCE(sat)	IC=-500mA, IB=-50mA			-0.6	V
Base-emitter saturation voltage	VBE(sat)	IC=-500mA, IB=-50mA			-1.2	V
Transition frequency	fT	VCE=-6V, IC=20mA, f=30MHZ	150			MHz